

STARPOWER

SEMICONDUCTOR

MOSFET

MD200HFR120C2S

1200V/200A 2 in one-package

General Description

STARPOWER MOSFET Power Module provides very low $R_{DS(on)}$ as well as optimized intrinsic diode. It's designed for the applications such SMPS and DC drives.

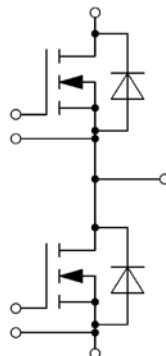
Features

- SiC power MOSFET
- Low $R_{DS(on)}$
- Optimized intrinsic reverse diode
- Chip sintering technology
- Low inductance case avoid oscillations
- Isolated copper baseplate using AlN DBC technology

Typical Applications

- Main and auxiliary AC drives of electric vehicles
- DC servo and robot drives
- Battery vehicles
- UPS equipment
- Plasma cutting

Equivalent Circuit Schematic



Absolute Maximum Ratings

MOSFET

Symbol	Description	Value	Unit
V_{DSS}	Drain-Source Voltage	1200	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current @ $T_C=25^\circ\text{C}$ @ $T_C=105^\circ\text{C}$	299	A
		200	A
I_{DM}	Pulsed Drain Current	822	A

Inverse Diode

Symbol	Description	Value	Unit
I_S	Source Current	200	A
I_{SM}	Pulsed Source Current	822	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V

MOSFET Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$R_{DS(on)}$	Static Drain-Source On-Resistance	$I_D=120A, V_{GS}=18V, T_j=25^\circ C$		6.7	8.7	m Ω
		$I_D=120A, V_{GS}=18V, T_j=125^\circ C$		10.0		
$V_{GS(th)}$	Gate-Source Threshold Voltage	$I_D=60mA, V_{DS}=V_{GS}, T_j=25^\circ C$	2.7		5.6	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=120A$		49.8		S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=V_{DSS}, V_{GS}=0V, T_j=25^\circ C$			60	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=V_{GSS}, V_{DS}=0V, T_j=25^\circ C$			0.6	μA
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=800V, f=1MHz$		8.0		nF
C_{oss}	Output Capacitance			0.46		nF
C_{rss}	Reverse Transfer Capacitance			0.16		nF
Q_g	Total Gate Charge	$I_D=120A, V_{DS}=600V, V_{GS}=18V$		642		nC
Q_{gs}	Gate-Source Charge			132		nC
Q_{gd}	Gate-Drain ("Miller") Charge			246		nC
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=400V, I_D=108A, R_G=0\Omega, V_{GS}=18V, T_j=25^\circ C$		21		ns
t_r	Rise Time			39		ns
$t_{d(off)}$	Turn-Off Delay Time			49		ns
t_f	Fall Time			24		ns
E_{on}	Turn-On Switching Loss	$V_{DS}=600V, I_D=120A, R_G=0\Omega, V_{GS}=18V, T_j=25^\circ C$		1.70		mJ
E_{off}	Turn-Off Switching Loss			0.71		mJ

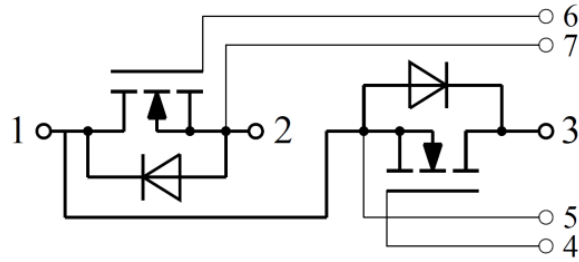
Inverse Diode Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage	$I_S=120A, V_{GS}=0V, T_j=25^\circ C$		3.2		V
t_{rr}	Diode Reverse Recovery Time	$V_R=600V, I_S=120A, -di/dt=6600A/\mu s, T_j=25^\circ C$		25		ns
Q_r	Diode Reverse Recovery Charge			0.69		μC
I_{RM}	Peak Reverse Recovery Current			54		A

Module Characteristics $T_c=25^{\circ}\text{C}$ unless otherwise noted

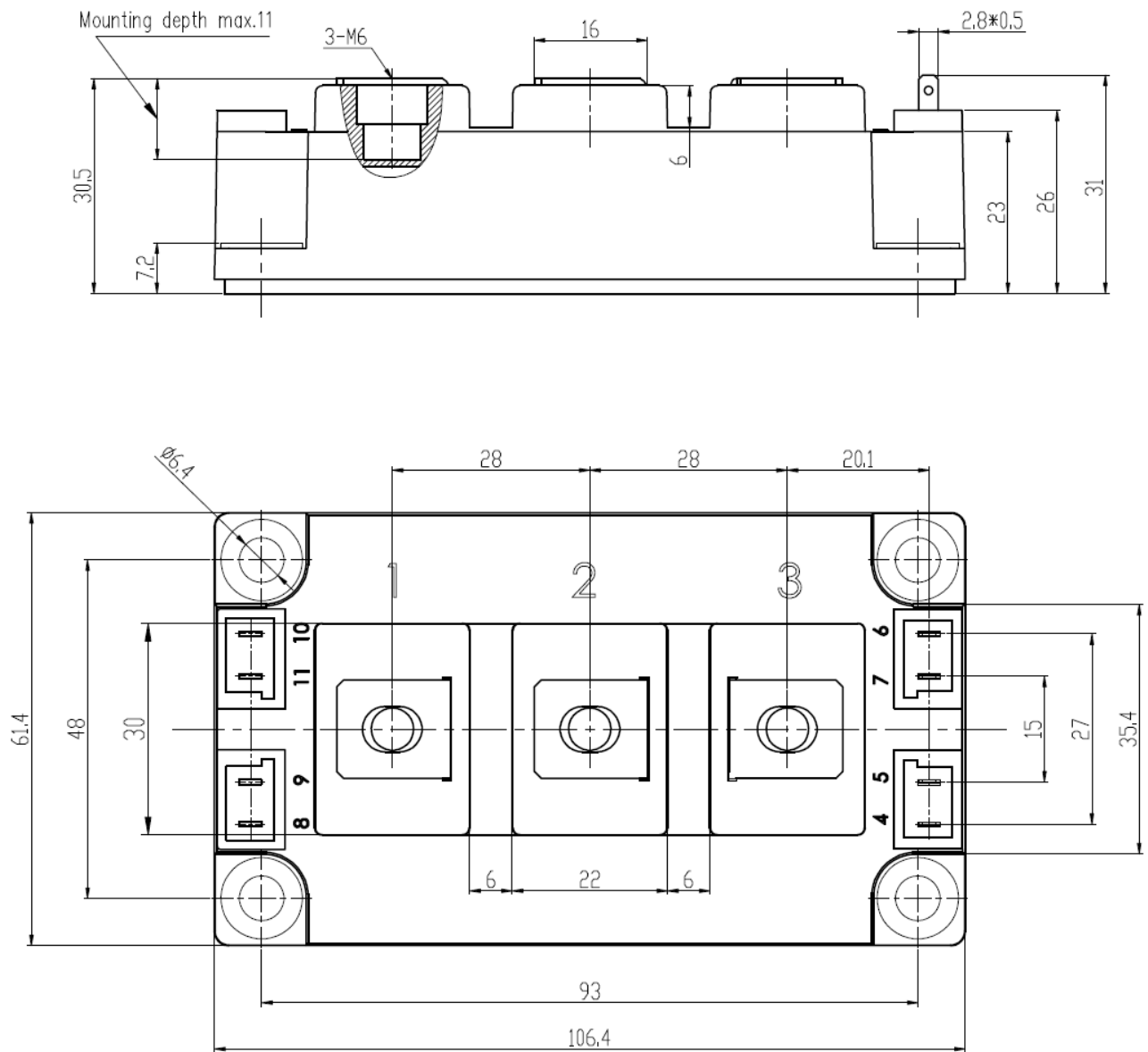
Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case(Mosfet)			0.122	K/W
R_{thCH}	Case-to-Heatsink (Mosfet)		0.020		K/W
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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